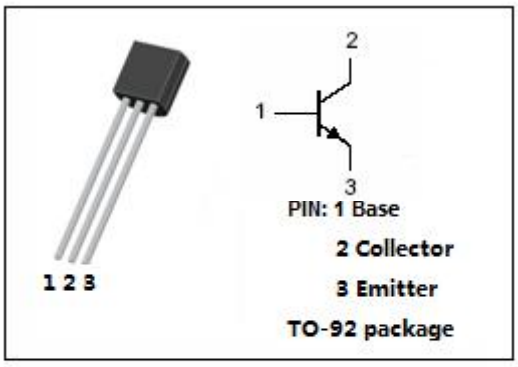
isc Silicon NPN Power Transistor 2SC2705

DESCRIPTION

- Collector-Emitter sustaining Voltage
  : V_{CEO}=150V(Min)
- Good Linearity of h_{FE}
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

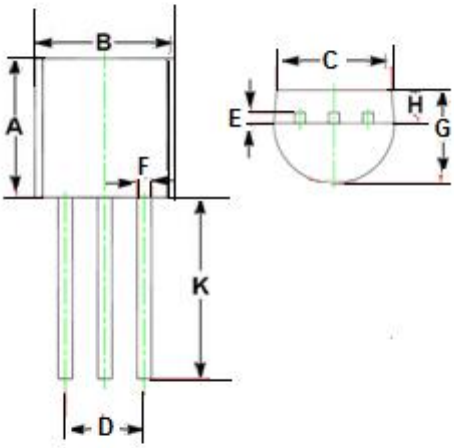


APPLICATIONS

- Audio Frequency Amplifier Applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	150	V
V_{CEO}	Collector-Emitter Voltage	150	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	50	mA
I_B	Base Current- Continuous	5	mA
P_C	Total Power Dissipation @ T_C=25℃	800	mW
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	4.30	4.70
B	4.30	4.70
C	3.43	
D	2.44	2.64
E	0.36	0.51
F	0.38	0.55
G	3.30	3.70
H	1.10	1.40
K	14.10	14.50

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(BR)}$	Collector-Emitter Breakdown Voltage	I_C=30mA ; I_B= 0	150			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 10mA; I_B= 1mA			1.0	V
$V_{BE(sat)}$	Base-Emitter Voltage	I_C= 10mA; V_{CE}=5V			0.8	V
I_{CEO}	Collector Cutoff Current	V_{CE}= 150V ; I_E= 0			0.1	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}=5V; I_C= 0			0.1	μA
h_{FE}	DC Current Gain	I_C=10mA ; V_{CE}=5V	80		240	